

George Cirlin

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306
papers

4,211
citations

34
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57
g-index

333
ext. papers

4,615
ext. citations

1.9
avg, IF

5.05
L-index

| # | Paper | IF | Citations |
|-----|---|------|-----------|
| 306 | Diffusion-induced growth of GaAs nanowiskers during molecular beam epitaxy: Theory and experiment. <i>Physical Review B</i> , 2005 , 71, | 3.3 | 258 |
| 305 | Self-catalyzed, pure zinblende GaAs nanowires grown on Si(111) by molecular beam epitaxy. <i>Physical Review B</i> , 2010 , 82, | 3.3 | 179 |
| 304 | Theoretical analysis of the vapor-liquid-solid mechanism of nanowire growth during molecular beam epitaxy. <i>Physical Review E</i> , 2006 , 73, 021603 | 2.4 | 154 |
| 303 | Gibbs-Thomson and diffusion-induced contributions to the growth rate of Si, InP, and GaAs nanowires. <i>Physical Review B</i> , 2009 , 79, | 3.3 | 147 |
| 302 | Semiconductor nanowiskers: Synthesis, properties, and applications. <i>Semiconductors</i> , 2009 , 43, 1539-1584 | 3.4 | 146 |
| 301 | New mode of vapor-liquid-solid nanowire growth. <i>Nano Letters</i> , 2011 , 11, 1247-53 | 11.5 | 125 |
| 300 | Au-assisted molecular beam epitaxy of InAs nanowires: Growth and theoretical analysis. <i>Journal of Applied Physics</i> , 2007 , 102, 094313 | 2.5 | 123 |
| 299 | Critical diameters and temperature domains for MBE growth of III-V nanowires on lattice mismatched substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009 , 3, 112-114 | 2.5 | 108 |
| 298 | Kinetics of the initial stage of coherent island formation in heteroepitaxial systems. <i>Physical Review B</i> , 2003 , 68, | 3.3 | 104 |
| 297 | Growth of GaN free-standing nanowires by plasma-assisted molecular beam epitaxy: structural and optical characterization. <i>Nanotechnology</i> , 2007 , 18, 385306 | 3.4 | 103 |
| 296 | Growth and characterization of InP nanowires with InAsP insertions. <i>Nano Letters</i> , 2007 , 7, 1500-4 | 11.5 | 102 |
| 295 | Temperature conditions for GaAs nanowire formation by Au-assisted molecular beam epitaxy. <i>Nanotechnology</i> , 2006 , 17, 4025-30 | 3.4 | 101 |
| 294 | Role of nonlinear effects in nanowire growth and crystal phase. <i>Physical Review B</i> , 2009 , 80, | 3.3 | 83 |
| 293 | Facet and in-plane crystallographic orientations of GaN nanowires grown on Si(111). <i>Nanotechnology</i> , 2008 , 19, 155704 | 3.4 | 77 |
| 292 | Anapoles in Free-Standing III-V Nanodisks Enhancing Second-Harmonic Generation. <i>Nano Letters</i> , 2018 , 18, 3695-3702 | 11.5 | 75 |
| 291 | Ordering phenomena in InAs strained layer morphological transformation on GaAs (100) surface. <i>Applied Physics Letters</i> , 1995 , 67, 97-99 | 3.4 | 63 |
| 290 | GaAs nanowires formed by Au-assisted molecular beam epitaxy: Effect of growth temperature. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 853-856 | 1.6 | 61 |

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| 289 | Optical properties of InAs quantum dots in a Si matrix. <i>Applied Physics Letters</i> , 1999 , 74, 1701-1703 | 3.4 | 61 |
| 288 | Wurtzite to zinc blende phase transition in GaAs nanowires induced by epitaxial burying. <i>Nano Letters</i> , 2008 , 8, 1638-43 | 11.5 | 60 |
| 287 | Diffusion-controlled growth of semiconductor nanowires: Vapor pressure versus high vacuum deposition. <i>Surface Science</i> , 2007 , 601, 4395-4401 | 1.8 | 53 |
| 286 | Shape modification of III-V nanowires: the role of nucleation on sidewalls. <i>Physical Review E</i> , 2008 , 77, 031606 | 2.4 | 52 |
| 285 | Atomic structure of MBE-grown GaAs nanowhiskers. <i>Physics of the Solid State</i> , 2005 , 47, 2213 | 0.8 | 52 |
| 284 | Photovoltaic Properties of p-Doped GaAs Nanowire Arrays Grown on n-Type GaAs(111)B Substrate. <i>Nanoscale Research Letters</i> , 2009 , 5, 360-3 | 5 | 49 |
| 283 | Formation of InAs quantum dots on a silicon (100) surface. <i>Semiconductor Science and Technology</i> , 1998 , 13, 1262-1265 | 1.8 | 46 |
| 282 | The role of surface diffusion of adatoms in the formation of nanowire crystals. <i>Semiconductors</i> , 2006 , 40, 1075-1082 | 0.7 | 45 |
| 281 | Room-temperature light emission from a highly strained Si/Ge superlattice. <i>Applied Physics Letters</i> , 2003 , 83, 3084-3086 | 3.4 | 44 |
| 280 | Photovoltaic properties of GaAsP core-shell nanowires on Si(001) substrate. <i>Nanotechnology</i> , 2012 , 23, 265402 | 3.4 | 42 |
| 279 | Reversibility of the island shape, volume and density in Stranski-Krastanow growth. <i>Semiconductor Science and Technology</i> , 2001 , 16, 502-506 | 1.8 | 42 |
| 278 | On the non-monotonic lateral size dependence of the height of GaAs nanowhiskers grown by molecular beam epitaxy at high temperature. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, R30-R33 | 1.3 | 41 |
| 277 | Influence of shadow effect on the growth and shape of InAs nanowires. <i>Journal of Applied Physics</i> , 2012 , 111, 104317 | 2.5 | 40 |
| 276 | Inorganic photovoltaics [Planar and nanostructured devices]. <i>Progress in Materials Science</i> , 2016 , 82, 294-404 | 42.2 | 38 |
| 275 | Polar Second-Harmonic Imaging to Resolve Pure and Mixed Crystal Phases along GaAs Nanowires. <i>Nano Letters</i> , 2016 , 16, 6290-6297 | 11.5 | 36 |
| 274 | Photoluminescence properties of InAs nanowires grown on GaAs and Si substrates. <i>Nanotechnology</i> , 2010 , 21, 335705 | 3.4 | 35 |
| 273 | The diffusion mechanism in the formation of GaAs and AlGaAs nanowhiskers during the process of molecular-beam epitaxy. <i>Semiconductors</i> , 2005 , 39, 557-564 | 0.7 | 35 |
| 272 | Miniband-related 1.4-1.8 μm luminescence of Ge/Si quantum dot superlattices. <i>Nanoscale Research Letters</i> , 2006 , 1, 137-153 | 5 | 34 |

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| 271 | Structure and optical properties of Si/InAs/Si layers grown by molecular beam epitaxy on Si substrate. <i>Applied Physics Letters</i> , 2000 , 76, 2677-2679 | 3.4 | 28 |
| 270 | Origin of Spontaneous Core-Shell AlGaAs Nanowires Grown by Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , 2016 , 16, 7251-7255 | 3.5 | 27 |
| 269 | Kinetic model of the growth of nanodimensional whiskers by the vapor-liquid-crystal mechanism. <i>Technical Physics Letters</i> , 2004 , 30, 682-686 | 0.7 | 27 |
| 268 | Photoluminescence properties of GaAs nanowire ensembles with zincblende and wurtzite crystal structure. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 175-177 | 2.5 | 26 |
| 267 | Dopant-stimulated growth of GaN nanotube-like nanostructures on Si(111) by molecular beam epitaxy. <i>Beilstein Journal of Nanotechnology</i> , 2018 , 9, 146-154 | 3 | 25 |
| 266 | Terahertz generation by GaAs nanowires. <i>Applied Physics Letters</i> , 2013 , 103, 072108 | 3.4 | 25 |
| 265 | Room temperature electroluminescence from Ge/Si quantum dots superlattice close to 1.6 μm . <i>Physica Status Solidi A</i> , 2003 , 198, R4-R6 | | 25 |
| 264 | Droplet epitaxy mediated growth of GaN nanostructures on Si (111) via plasma-assisted molecular beam epitaxy. <i>CrystEngComm</i> , 2018 , 20, 3370-3380 | 3.3 | 23 |
| 263 | Numerical modeling of photovoltaic efficiency of n-type GaN nanowires on p-type Si heterojunction. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015 , 9, 507-510 | 2.5 | 23 |
| 262 | Optical study of GaAs quantum dots embedded into AlGaAs nanowires. <i>Semiconductor Science and Technology</i> , 2012 , 27, 015009 | 1.8 | 23 |
| 261 | Effects of the surface preparation and buffer layer on the morphology, electronic and optical properties of the GaN nanowires on Si. <i>Nanotechnology</i> , 2019 , 30, 395602 | 3.4 | 22 |
| 260 | Transient carrier transfer in tunnel injection structures. <i>Applied Physics Letters</i> , 2008 , 93, 031105 | 3.4 | 21 |
| 259 | Nanowire Quantum Dots Tuned to Atomic Resonances. <i>Nano Letters</i> , 2018 , 18, 7217-7221 | 11.5 | 21 |
| 258 | Growth and Characterization of GaP/GaPAs Nanowire Heterostructures with Controllable Composition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900350 | 2.5 | 19 |
| 257 | Study of processes of self-catalyzed growth of GaAs crystal nanowires by molecular-beam epitaxy on modified Si (111) surfaces. <i>Semiconductors</i> , 2011 , 45, 431-435 | 0.7 | 19 |
| 256 | Terahertz radiation generation in multilayer quantum-cascade heterostructures. <i>Technical Physics Letters</i> , 2017 , 43, 362-365 | 0.7 | 18 |
| 255 | Growth of Inclined GaAs Nanowires by Molecular Beam Epitaxy: Theory and Experiment. <i>Nanoscale Research Letters</i> , 2010 , 5, 1692-7 | 5 | 18 |
| 254 | Control over the parameters of InAs-GaAs quantum dot arrays in the Stranski-Krastanow growth mode. <i>Semiconductors</i> , 2003 , 37, 861-865 | 0.7 | 18 |

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| 253 | Unified mechanism of the surface Fermi level pinning in III-As nanowires. <i>Nanotechnology</i> , 2018 , 29, 314003 | 3 | 17 |
| 252 | AlGaAs and AlGaAs/GaAs/AlGaAs nanowires grown by molecular beam epitaxy on silicon substrates. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 484003 | 3 | 15 |
| 251 | Hybrid AlGaAs/GaAs/AlGaAs nanowires with a quantum dot grown by molecular beam epitaxy on silicon. <i>Semiconductors</i> , 2016 , 50, 1421-1424 | 0.7 | 15 |
| 250 | Generation of terahertz radiation in ordered arrays of GaAs nanowires. <i>Applied Physics Letters</i> , 2015 , 106, 252104 | 3.4 | 15 |
| 249 | GaN/AlN free-standing nanowires grown by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1556-1558 | | 15 |
| 248 | Temperature dependence of the quantum dot lateral size in the Ge/Si(100) system. <i>Physica Status Solidi (B): Basic Research</i> , 2003 , 236, R1-R3 | 1.3 | 15 |
| 247 | Modified silicone rubber for fabrication and contacting of flexible suspended membranes of n-/p-GaP nanowires with a single-walled carbon nanotube transparent contact. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 3764-3772 | 7.1 | 15 |
| 246 | Nanospectroscopic Imaging of Twinning Superlattices in an Individual GaAs-AlGaAs Core-Shell Nanowire. <i>ACS Photonics</i> , 2014 , 1, 1099-1106 | 6.3 | 14 |
| 245 | Ordering of nanostructures in a Si/Ge _{0.3} Si _{0.7} /Ge system during molecular beam epitaxy. <i>Semiconductors</i> , 2002 , 36, 1294-1298 | 0.7 | 14 |
| 244 | Growth kinetics of thin films formed by nucleation during layer formation. <i>Semiconductors</i> , 2005 , 39, 1267 | 0.7 | 14 |
| 243 | Photoluminescence of isolated quantum dots in metastable InAs arrays. <i>Nanotechnology</i> , 2002 , 13, 143-148 | 3.4 | 14 |
| 242 | Microlens-Enhanced Substrate Patterning and MBE Growth of GaP Nanowires. <i>Semiconductors</i> , 2018 , 52, 2088-2091 | 0.7 | 14 |
| 241 | Fabrication of a terahertz quantum-cascade laser with a double metal waveguide based on multilayer GaAs/AlGaAs heterostructures. <i>Semiconductors</i> , 2016 , 50, 1377-1382 | 0.7 | 13 |
| 240 | Fabrication of InAs quantum dots on silicon. <i>Technical Physics Letters</i> , 1998 , 24, 290-292 | 0.7 | 13 |
| 239 | Ferromagnetic (Ga,Mn)As nanowires grown by Mn-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2013 , 113, 144303 | 2.5 | 12 |
| 238 | Thermally assisted tunneling processes in In _x Ga _{1-x} As/GaAs quantum-dot structures. <i>Physical Review B</i> , 2006 , 74, | 3.3 | 12 |
| 237 | Energy spectrum and thermal properties of a terahertz quantum-cascade laser based on the resonant-phonon depopulation scheme. <i>Semiconductors</i> , 2017 , 51, 514-519 | 0.7 | 11 |
| 236 | Control of Conductivity of InGaAs Nanowires by Applied Tension and Surface States. <i>Nano Letters</i> , 2019 , 19, 4463-4469 | 11.5 | 11 |

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| 235 | Formation of (Ga,Mn)As nanowires and study of their magnetic properties. <i>Semiconductors</i> , 2012 , 46, 179-183 | 0.7 | 11 |
| 234 | Effect of diffusion from a lateral surface on the rate of GaN nanowire growth. <i>Semiconductors</i> , 2012 , 46, 838-841 | 0.7 | 11 |
| 233 | Si Incorporation in InP Nanowires Grown by Au-Assisted Molecular Beam Epitaxy. <i>Journal of Nanomaterials</i> , 2009 , 2009, 1-7 | 3.2 | 11 |
| 232 | Influence of substrate temperature on the shape of GaAs nanowires grown by Au-assisted MOVPE. <i>Journal of Crystal Growth</i> , 2010 , 312, 1676-1682 | 1.6 | 11 |
| 231 | Electron diffraction on GaAs nanowhiskers grown on Si(100) and Si(111) substrates by molecular-beam epitaxy. <i>Physics of the Solid State</i> , 2007 , 49, 1440-1445 | 0.8 | 11 |
| 230 | Self-Catalyzed MBE-Grown GaP Nanowires on Si(111): V/III Ratio Effects on the Morphology and Crystal Phase Switching. <i>Semiconductors</i> , 2018 , 52, 2092-2095 | 0.7 | 11 |
| 229 | Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012115 | 0.3 | 10 |
| 228 | Growth and optical properties of filamentary GaN nanocrystals grown on a hybrid SiC/Si(111) substrate by molecular beam epitaxy. <i>Physics of the Solid State</i> , 2016 , 58, 1952-1955 | 0.8 | 10 |
| 227 | Effect of postgrowth heat treatment on the structural and optical properties of InP/InAsP/InP nanowires. <i>Semiconductors</i> , 2012 , 46, 175-178 | 0.7 | 10 |
| 226 | Model of a GaAs Quantum Dot Embedded in a Polymorph AlGaAs Nanowire. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 1-9 | 3.8 | 10 |
| 225 | Composite system based on CdSe/ZnS quantum dots and GaAs nanowires. <i>Semiconductors</i> , 2013 , 47, 1346-1350 | 0.7 | 10 |
| 224 | Piezoelectric effect in GaAs nanowires. <i>Semiconductors</i> , 2011 , 45, 1082-1084 | 0.7 | 10 |
| 223 | Hexagonal structures in GaAs nanowhiskers. <i>Technical Physics Letters</i> , 2008 , 34, 538-541 | 0.7 | 10 |
| 222 | Baric properties of InAs quantum dots. <i>Semiconductors</i> , 2008 , 42, 1076-1083 | 0.7 | 10 |
| 221 | Piezoelectric Current Generation in Wurtzite GaAs Nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018 , 12, 1700358 | 2.5 | 10 |
| 220 | InP/Si Heterostructure for High-Current Hybrid Triboelectric/Photovoltaic Generation. <i>ACS Applied Energy Materials</i> , 2019 , 2, 4395-4401 | 6.1 | 9 |
| 219 | Coherent Growth of InP/InAsP/InP Nanowires on a Si (111) Surface by Molecular-Beam Epitaxy. <i>Technical Physics Letters</i> , 2018 , 44, 112-114 | 0.7 | 9 |
| 218 | Hybrid GaAs/AlGaAs Nanowire/Quantum dot System for Single Photon Sources. <i>Semiconductors</i> , 2018 , 52, 462-464 | 0.7 | 9 |

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| 217 | Sharp emission from single InAs quantum dots grown on vicinal GaAs surfaces. <i>Applied Physics Letters</i> , 2009 , 94, 163114 | 3.4 | 9 |
| 216 | The initial stage of growth of crystalline nanowhiskers. <i>Semiconductors</i> , 2010 , 44, 112-115 | 0.7 | 9 |
| 215 | Si/Ge nanostructures for optoelectronics applications. <i>Physics of the Solid State</i> , 2004 , 46, 49-55 | 0.8 | 9 |
| 214 | Threshold behavior of the formation of nanometer islands in a Ge/Si(100) system in the presence of Sb. <i>Semiconductors</i> , 2005 , 39, 547-551 | 0.7 | 9 |
| 213 | Thermal Penetration of Gold Nanoparticles into Silicon Dioxide. <i>Acta Physica Polonica A</i> , 2017 , 132, 366-369 | | 9 |
| 212 | Engineering of the Second-Harmonic Emission Directionality with III-V Semiconductor Rod Nanoantennas. <i>Laser and Photonics Reviews</i> , 2020 , 14, 2000028 | 8.3 | 9 |
| 211 | Numerical simulation of the properties of solar cells based on GaPNAs/Si heterostructures and GaN nanowires. <i>Semiconductors</i> , 2016 , 50, 1521-1525 | 0.7 | 8 |
| 210 | Piezoelectric effect in wurtzite GaAs nanowires: Growth, characterization, and electromechanical 3D modeling. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 3014-3019 | 1.6 | 8 |
| 209 | Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. <i>Materials Science in Semiconductor Processing</i> , 2016 , 55, 72-78 | 4.3 | 8 |
| 208 | Current-voltage characteristics of silicon-doped GaAs nanowhiskers with a protecting AlGaAs coating overgrown with an undoped GaAs layer. <i>Semiconductors</i> , 2010 , 44, 610-615 | 0.7 | 8 |
| 207 | Temperature dependent luminescence from quantum dot arrays: phonon-assisted line broadening versus carrier escape-induced narrowing. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 347-352 | 1.3 | 8 |
| 206 | Suppression of dome-shaped clusters during molecular beam epitaxy of Ge on Si(100). <i>Semiconductors</i> , 2004 , 38, 1202-1206 | 0.7 | 8 |
| 205 | GaSb/GaAs quantum dot systems: in situ synchrotron radiation x-ray photoelectron spectroscopy study. <i>Nanotechnology</i> , 2005 , 16, 1326-1334 | 3.4 | 8 |
| 204 | Piezoelectric effect in GaAs nanowires: experiment and theory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016 , 10, 172-175 | 2.5 | 8 |
| 203 | Light-emitting tunneling nanostructures based on quantum dots in a Si and GaAs matrix. <i>Semiconductors</i> , 2012 , 46, 1460-1470 | 0.7 | 7 |
| 202 | A3B5 nanowhiskers: MBE growth and properties. <i>European Physical Journal D</i> , 2006 , 56, 13-20 | | 7 |
| 201 | The effective thickness, temperature and growth rate behavior of quantum dot ensembles. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, R42-R45 | 1.3 | 7 |
| 200 | MBE-grown Si: Er light-emitting structures: Effect of epitaxial growth conditions on impurity concentration and photoluminescence. <i>Physics of the Solid State</i> , 2005 , 47, 113 | 0.8 | 7 |

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| 199 | Multilayer heterostructures for quantum-cascade lasers operating in the terahertz frequency range. <i>Semiconductors</i> , 2016 , 50, 662-666 | 0.7 | 7 |
| 198 | Photoelectric properties of an array of axial GaAs/AlGaAs nanowires. <i>Technical Physics Letters</i> , 2015 , 41, 443-447 | 0.7 | 6 |
| 197 | Structural and Optical Properties of Self-Catalyzed Axially Heterostructured GaPN/GaP Nanowires Embedded into a Flexible Silicone Membrane. <i>Nanomaterials</i> , 2020 , 10, | 5.4 | 6 |
| 196 | Effect of the Uniaxial Compression on the GaAs Nanowire Solar Cell. <i>Micromachines</i> , 2020 , 11, | 3.3 | 6 |
| 195 | Deep-Subwavelength Raman Imaging of the Strained GaP Nanowires. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 14054-14060 | 3.8 | 6 |
| 194 | GaAs Wurtzite Nanowires for Hybrid Piezoelectric Solar Cells. <i>Semiconductors</i> , 2018 , 52, 609-611 | 0.7 | 6 |
| 193 | MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate 2016 , | | 6 |
| 192 | (In,Mn)As quantum dots: Molecular-beam epitaxy and optical properties. <i>Semiconductors</i> , 2013 , 47, 1037-1040 | 1.4 | 6 |
| 191 | Tuning of the interdot resonance in stacked InAs quantum dot arrays by an external electric field. <i>Journal of Applied Physics</i> , 2006 , 100, 083704 | 2.5 | 6 |
| 190 | Intraband light absorption in InAs/GaAs quantum dots covered with InGaAs quantum wells. <i>Semiconductor Science and Technology</i> , 2006 , 21, 1341-1347 | 1.8 | 6 |
| 189 | Growth of GaAs nanowhisker arrays by magnetron sputtering on Si(111) substrates. <i>Technical Physics Letters</i> , 2006 , 32, 520-522 | 0.7 | 6 |
| 188 | Coupling of electron states in the InAs/GaAs quantum dot molecule. <i>Semiconductors</i> , 2006 , 40, 331-337 | 0.7 | 6 |
| 187 | Formation of GaAs nanowhisker arrays by magnetron sputtering deposition. <i>Physics of the Solid State</i> , 2006 , 48, 786-791 | 0.8 | 6 |
| 186 | Properties of GaAs nanowhiskers grown on a GaAs(111)B surface using a combined technique. <i>Semiconductors</i> , 2004 , 38, 1217-1220 | 0.7 | 6 |
| 185 | Optical properties of structures with ultradense arrays of Ge QDs in an Si matrix. <i>Semiconductors</i> , 2003 , 37, 210-214 | 0.7 | 6 |
| 184 | Localization of holes in an InAs/GaAs quantum-dot molecule. <i>Semiconductors</i> , 2005 , 39, 119 | 0.7 | 6 |
| 183 | The transition from thermodynamically to kinetically controlled formation of quantum dots in an InAs/GaAs(100) system. <i>Semiconductors</i> , 2005 , 39, 820-825 | 0.7 | 6 |
| 182 | Optical properties of submonolayer germanium clusters formed by molecular-beam epitaxy in a silicon matrix. <i>Technical Physics Letters</i> , 2001 , 27, 14-16 | 0.7 | 6 |

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| 181 | Fabrication and electrical study of large area free-standing membrane with embedded GaP NWs for flexible devices. <i>Nanotechnology</i> , 2020 , 31, 46LT01 | 3.4 | 6 |
| 180 | Nonradiative Energy Transfer in Hybrid Nanostructures with Varied Dimensionality. <i>Semiconductors</i> , 2019 , 53, 1258-1261 | 0.7 | 5 |
| 179 | Hydrogen passivation of the n-GaN nanowire/p-Si heterointerface. <i>Nanotechnology</i> , 2020 , 31, 244003 | 3.4 | 5 |
| 178 | The Role of Physical Models in the Description of Luminescence Kinetics of Hybrid Nanowires. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2020 , 128, 119-124 | 0.7 | 5 |
| 177 | A new insight into the mechanism of low-temperature Au-assisted growth of InAs nanowires. <i>CrystEngComm</i> , 2019 , 21, 4707-4717 | 3.3 | 5 |
| 176 | Specific features of Raman spectra of III ν nanowhiskers. <i>Physics of the Solid State</i> , 2011 , 53, 1431-1439 | 0.8 | 5 |
| 175 | On diffusion lengths of Ga adatoms on AlAs(111) and GaAs(111) surfaces. <i>Technical Physics</i> , 2009 , 54, 586-589 | 0.5 | 5 |
| 174 | DLTS study of the Wannier-Stark effect in Ge/Si QD superlattices. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 576-579 | 2.8 | 5 |
| 173 | Effect of deposition conditions on nanowhisker morphology. <i>Semiconductors</i> , 2007 , 41, 865-874 | 0.7 | 5 |
| 172 | Influence of MBE growth conditions on the surface morphology of Al(Ga)As nanowhiskers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 1365-1369 | 1.6 | 5 |
| 171 | Dependence of structural and optical properties of QD arrays in an InAs/GaAs system on surface temperature and growth rate. <i>Semiconductors</i> , 2004 , 38, 329-334 | 0.7 | 5 |
| 170 | Influence of antimony on the morphology and properties of an array of Ge/Si(100) quantum dots. <i>Physics of the Solid State</i> , 2005 , 47, 58 | 0.8 | 5 |
| 169 | Stoichiometry and absolute atomic concentration profiles obtained by combined Rutherford backscattering spectroscopy and secondary-ion mass spectroscopy: InAs nanocrystals in Si. <i>Nanotechnology</i> , 2002 , 13, 631-634 | 3.4 | 5 |
| 168 | Selective-Area Growth of GaN Nanowires on Patterned SiO $_x$ /Si Substrates by Molecular Beam Epitaxy. <i>Technical Physics Letters</i> , 2020 , 46, 1080-1083 | 0.7 | 5 |
| 167 | Terahertz Quantum-Cascade Laser Based on the Resonant-Phonon Depopulation Scheme. <i>International Journal of High Speed Electronics and Systems</i> , 2016 , 25, 1640022 | 0.5 | 5 |
| 166 | New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. <i>Nanotechnology</i> , 2018 , 29, 045602 | 3.4 | 5 |
| 165 | InAs/InP core/shell nanowire gas sensor: Effects of InP shell on sensitivity and long-term stability. <i>Applied Surface Science</i> , 2019 , 498, 143756 | 6.7 | 4 |
| 164 | Tunnel injection emitter structures with barriers comprising nanobridges. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011 , 5, 385-387 | 2.5 | 4 |

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| 163 | InGaAs tunnel-injection structures with nanobridges: Excitation transfer and luminescence kinetics. <i>Semiconductors</i> , 2010 , 44, 1050-1058 | 0.7 | 4 |
| 162 | Charge and spin storage in self-organized quantum dots. <i>Applied Physics Letters</i> , 2006 , 88, 182107 | 3.4 | 4 |
| 161 | The theory of the formation of multilayered thin films on solid surfaces. <i>Semiconductors</i> , 2006 , 40, 249-256 | | 4 |
| 160 | Quantum dots in InAs layers of subcritical thickness on GaAs(100). <i>Technical Physics Letters</i> , 2003 , 29, 691-693 | 0.7 | 4 |
| 159 | 1.3-1.4 μm photoluminescence emission from InAs/GaAs quantum dot multilayer structures grown on GaAs singular and vicinal substrates. <i>Nanotechnology</i> , 2000 , 11, 323-326 | 3.4 | 4 |
| 158 | Luminescence Photodynamics of Hybrid-Structured InP/InAsP/InP Nanowires Passivated by a Layer of TOPO-CdSe/ZnS Quantum Dots. <i>Semiconductors</i> , 2020 , 54, 1141-1146 | 0.7 | 4 |
| 157 | Resonant excitation of nanowire quantum dots. <i>Npj Quantum Information</i> , 2020 , 6, | 8.6 | 4 |
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